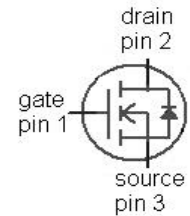


**OptiMOS<sup>®</sup> 2 Power-Transistor**
**Features**

- N-channel, logic level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target application
- Ideal for high-frequency switching and synchronous rectification

**Product Summary**

$V_{DS}$	100	V
$R_{DS(on),max}$	12	m $\Omega$
$I_D$	69	A



Type	IPP12CN10L G	IPS12CN10L G
<b>Package</b>	PG-TO220-3	PG-TO251-3-11
<b>Marking</b>	12CN10L	12CN10L

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}$	69	A
		$T_C=100\text{ °C}$	49	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	276	
Avalanche energy, single pulse	$E_{AS}$	$I_D=69\text{ A}$ , $R_{GS}=25\ \Omega$	150	mJ
Reverse diode $dv/dt$	$dv/dt$	$I_D=69\text{ A}$ , $V_{DS}=80\text{ V}$ , $di/dt=100\text{ A}/\mu\text{s}$ , $T_{j,max}=175\text{ °C}$	6	kV/ $\mu\text{s}$
Gate source voltage <sup>3)</sup>	$V_{GS}$		$\pm 20$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	125	W
Operating and storage temperature	$T_j$ , $T_{stg}$		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> see figure 3

<sup>3)</sup>  $T_{j,max}=150\text{ °C}$  and duty cycle  $D=0.01$  for  $V_{gs}<-5\text{ V}$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{thJC}$		-	-	1.2	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	minimal footprint	-	-	62	
		6 cm <sup>2</sup> cooling area <sup>4)</sup>	-	-	40	

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=83\text{ }\mu\text{A}$	1.2	1.84	2.4	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	$\mu\text{A}$
		$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}, I_D=34.5\text{ A},$ (TO220)	-	11.7	15.8	m $\Omega$
		$V_{GS}=10\text{ V}, I_D=69\text{ A},$ (TO220)	-	9.9	12	
		$V_{GS}=4.5\text{ V}, I_D=34.5\text{ A},$ (TO251)	-	11.7	15.8	
		$V_{GS}=10\text{ V}, I_D=69\text{ A},$ (TO251)	-	9.9	11.8	
Gate resistance	$R_G$		-	1.3	-	$\Omega$
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max},$ $I_D=69\text{ A}$	57	113	-	S

<sup>4)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V},$ $f=1\text{ MHz}$	-	4210	5600	pF
Output capacitance	$C_{oss}$		-	528	702	
Reverse transfer capacitance	$C_{rss}$		-	29	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$ $I_D=34.5\text{ A}, R_G=1.6\ \Omega$	-	14	-	ns
Rise time	$t_r$		-	9	-	
Turn-off delay time	$t_{d(off)}$		-	39	-	
Fall time	$t_f$		-	5	-	

**Gate Charge Characteristics<sup>5)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=50\text{ V}, I_D=69\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	16	-	nC
Gate to drain charge	$Q_{gd}$		-	10	-	
Switching charge	$Q_{sw}$		-	13	-	
Gate charge total	$Q_g$		-	58	-	
Gate plateau voltage	$V_{plateau}$		-	3.7	-	
Output charge	$Q_{oss}$	$V_{DD}=50\text{ V}, V_{GS}=0\text{ V}$	-	54	-	nC

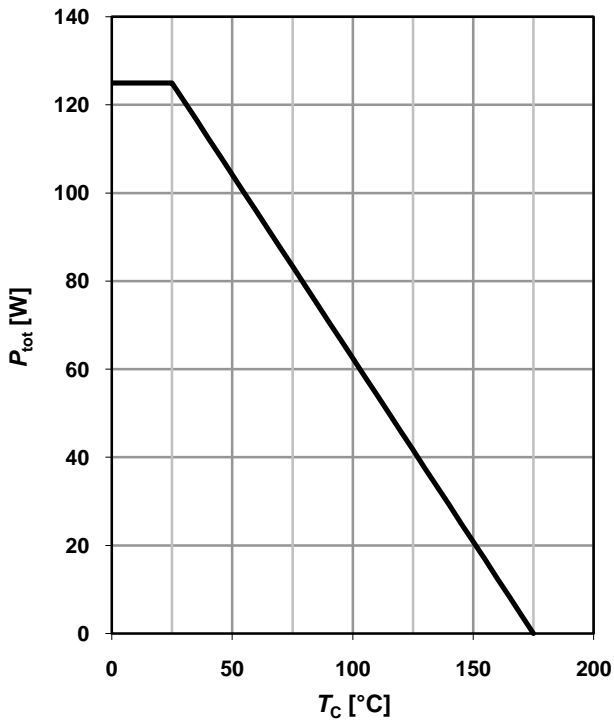
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ °C}$	-	-	69	A
Diode pulse current	$I_{S,pulse}$		-	-	276	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=69\text{ A},$ $T_j=25\text{ °C}$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=50\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	101	-	ns
Reverse recovery charge	$Q_{rr}$		-	193	-	nC

<sup>5)</sup> See figure 16 for gate charge parameter definition

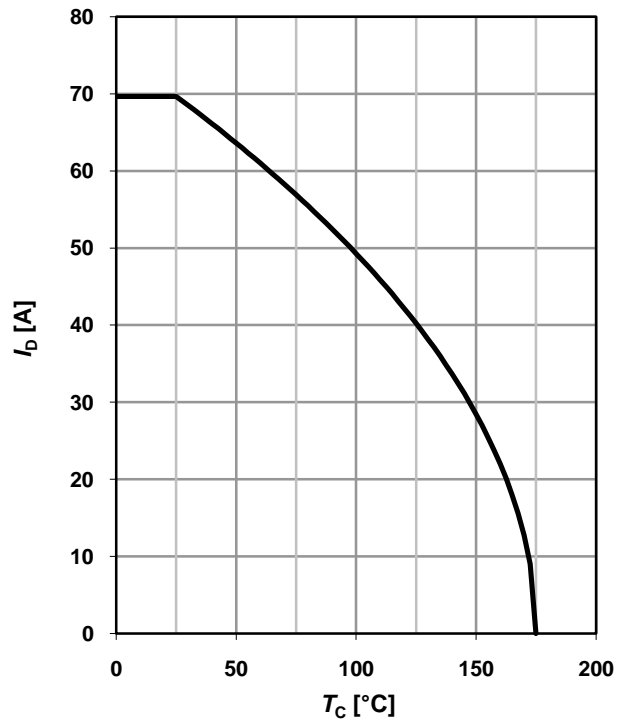
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



### 2 Drain current

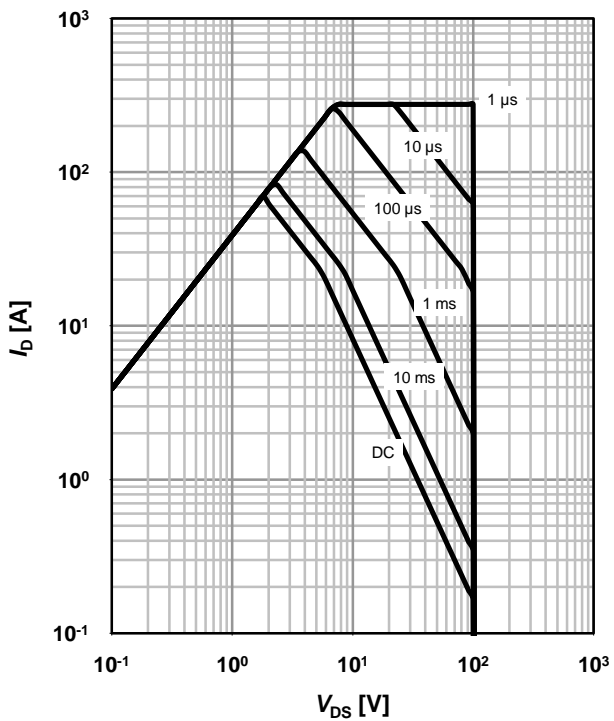
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

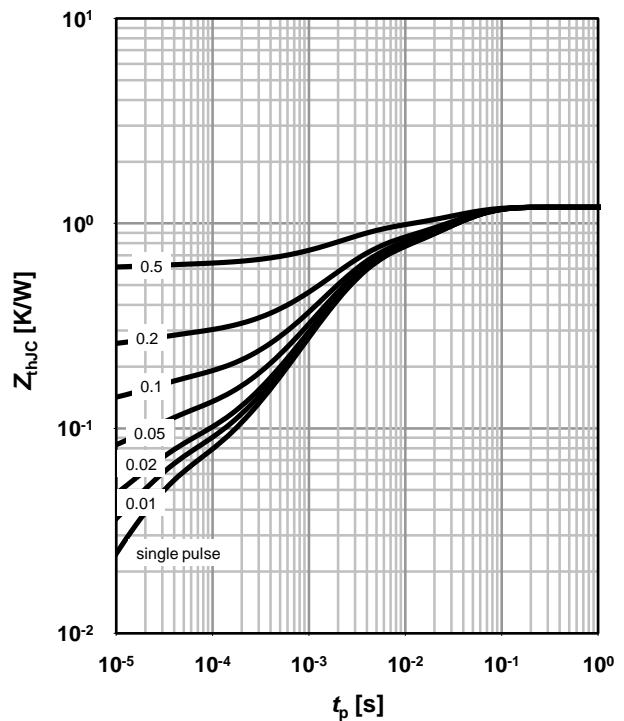
parameter:  $t_p$



### 4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

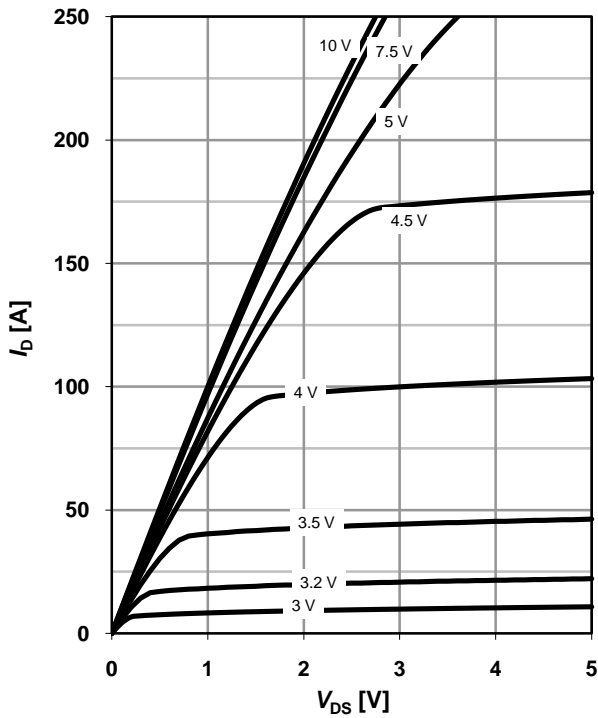
parameter:  $D = t_p/T$



### 5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25\text{ °C}$$

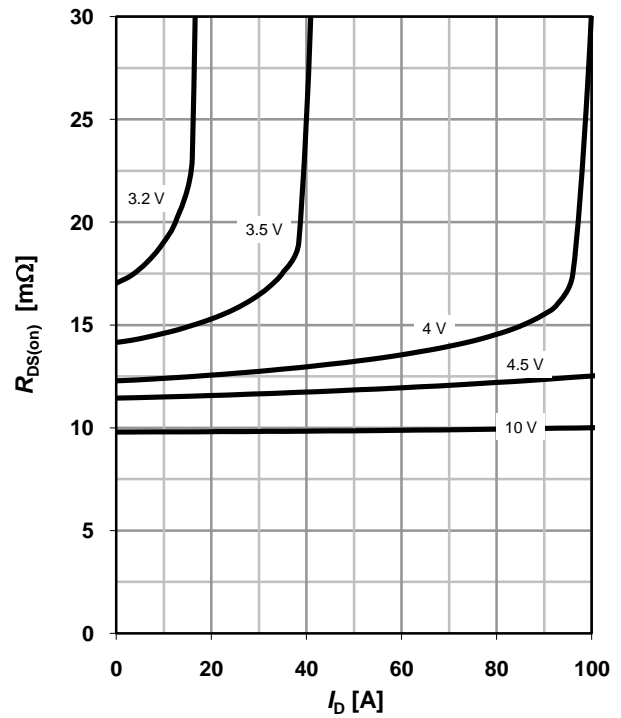
parameter:  $V_{GS}$



### 6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$$

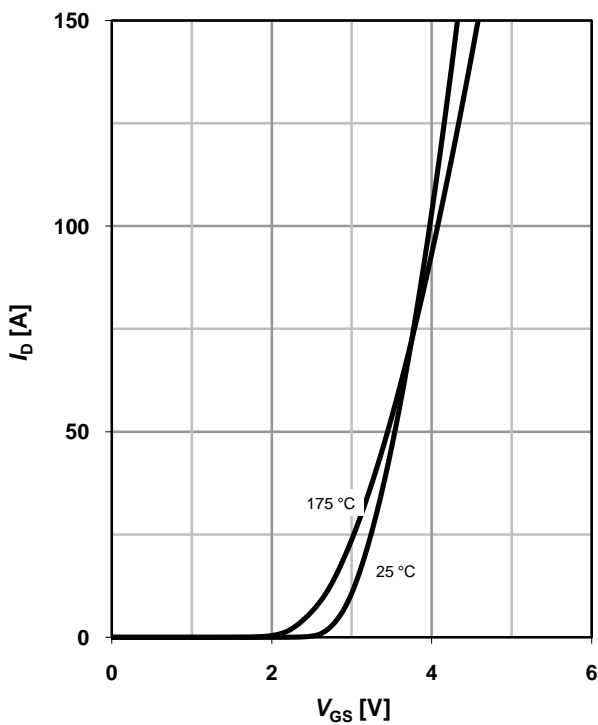
parameter:  $V_{GS}$



### 7 Typ. transfer characteristics

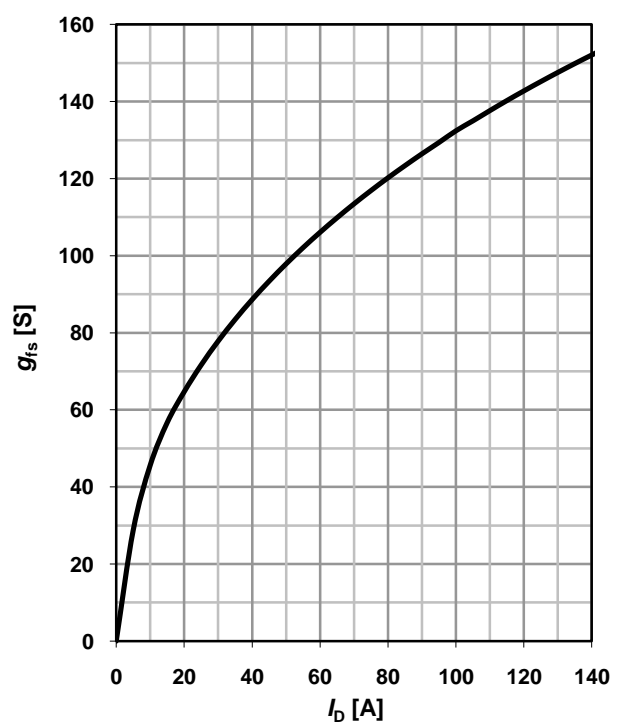
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

parameter:  $T_j$



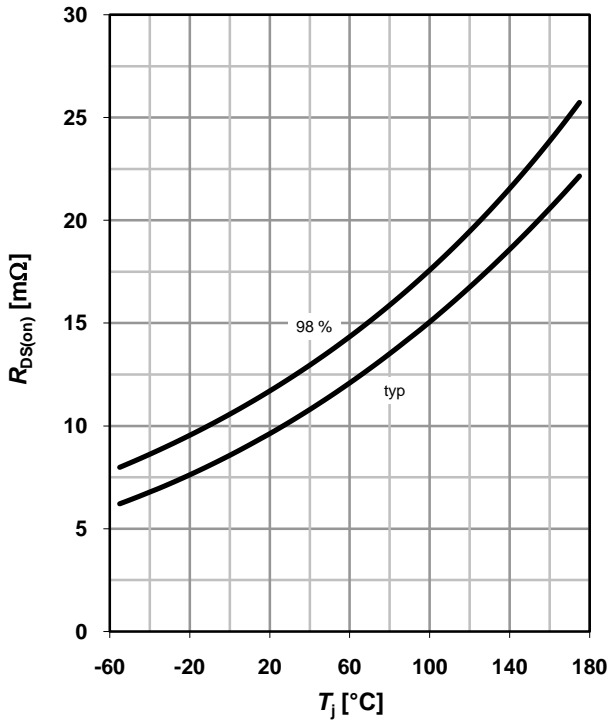
### 8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25\text{ °C}$$



**9 Drain-source on-state resistance**

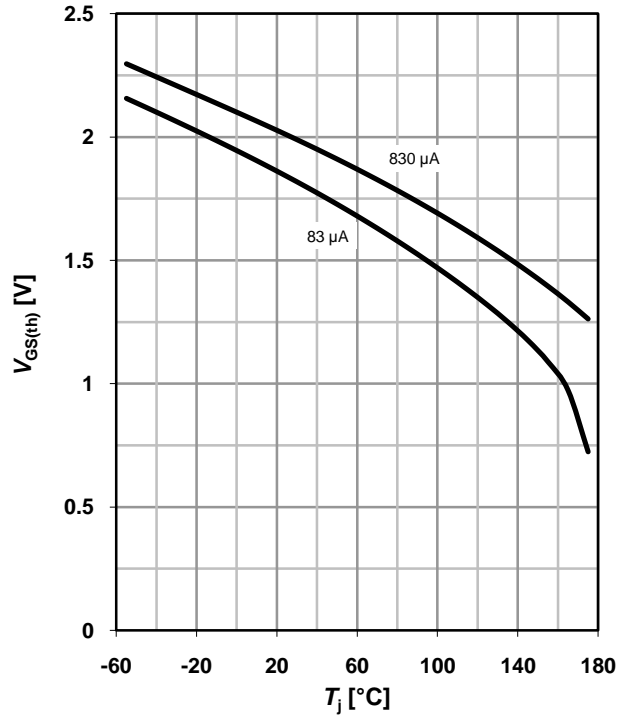
$R_{DS(on)}=f(T_j); I_D=69\text{ A}; V_{GS}=10\text{ V}$



**10 Typ. gate threshold voltage**

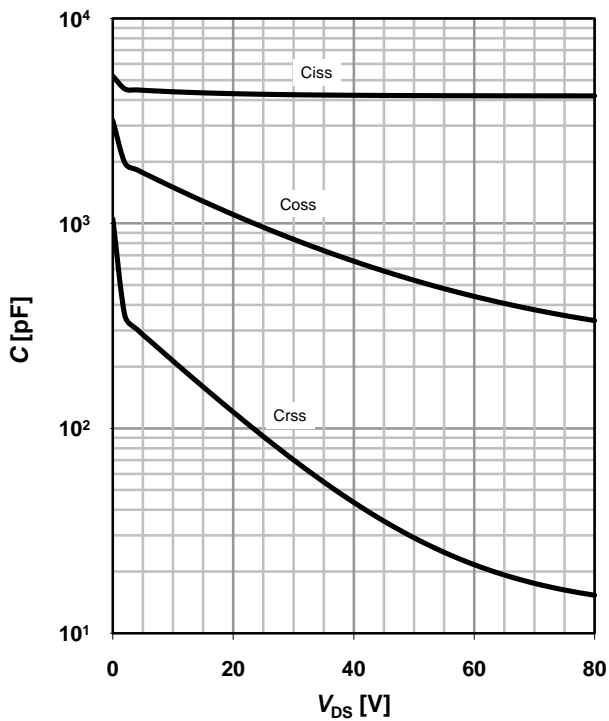
$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

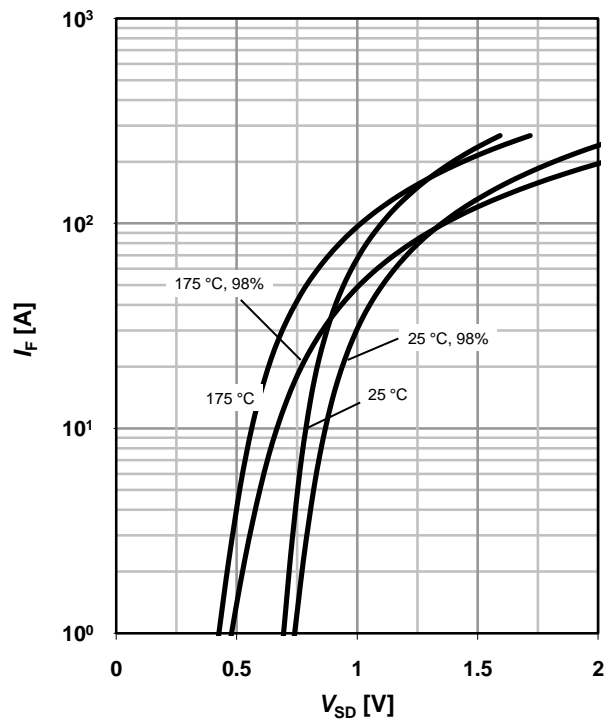
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

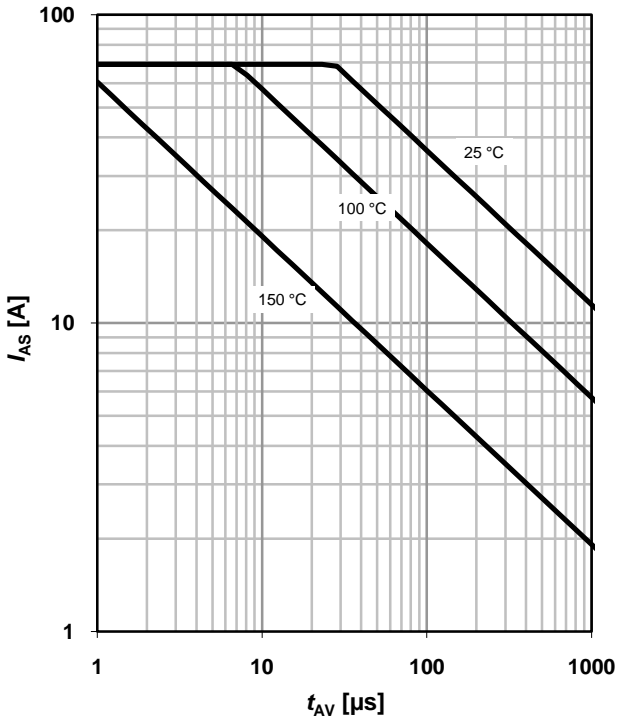
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

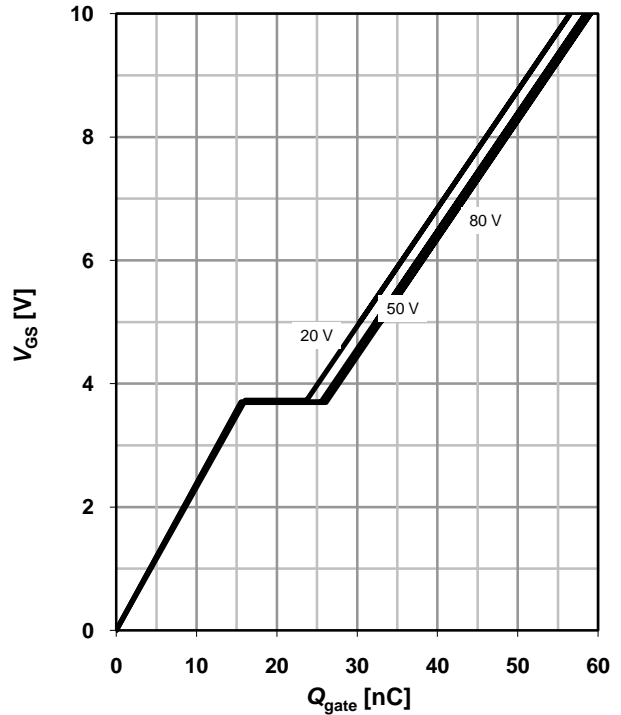
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

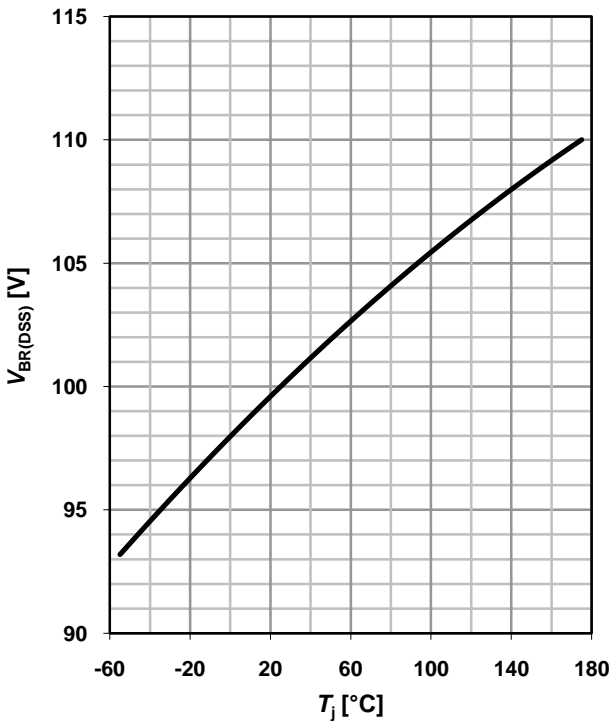
$V_{GS}=f(Q_{\text{gate}}); I_D=69 \text{ A pulsed}$

parameter:  $V_{DD}$



**15 Drain-source breakdown voltage**

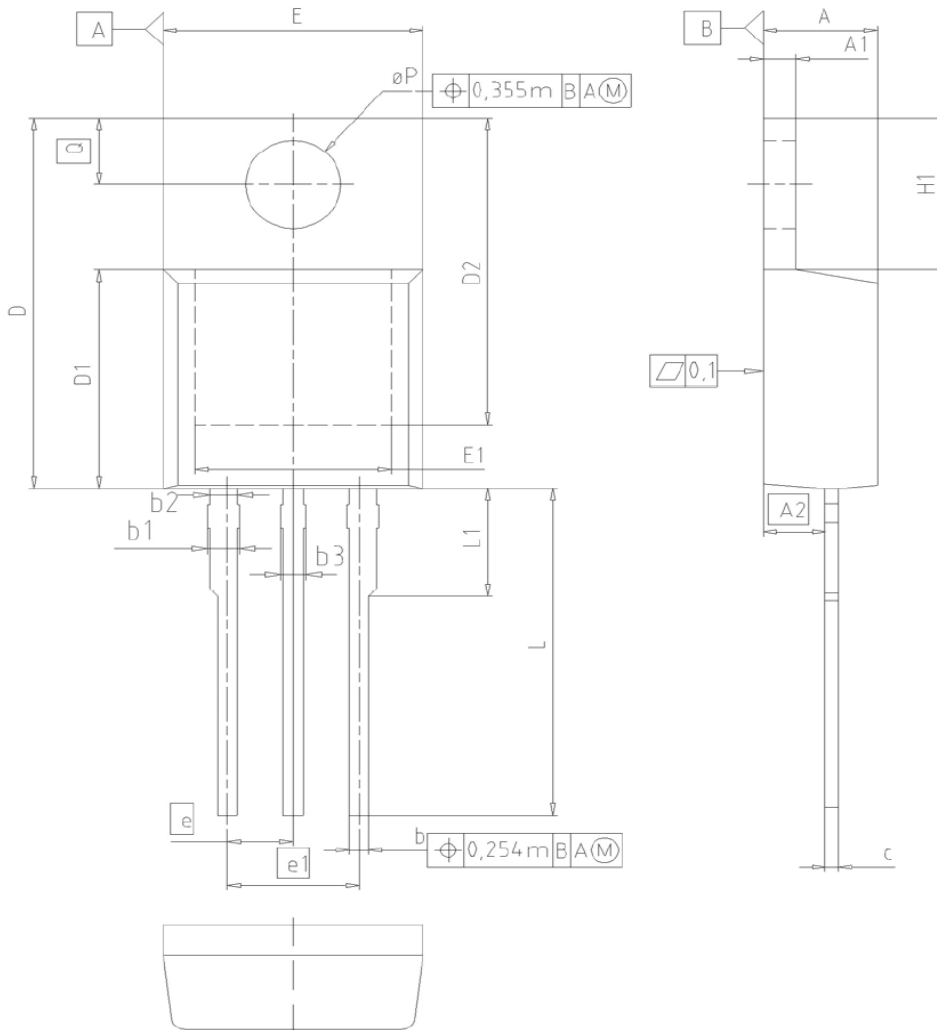
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



**16 Gate charge waveforms**



PG-TO220-3: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
$\phi P$	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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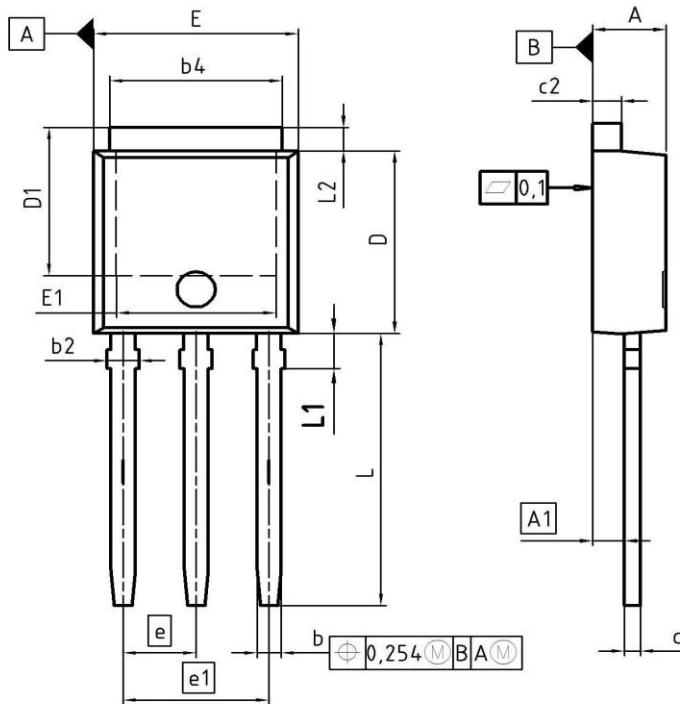
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DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.90	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.77	0.198	0.227
E	6.35	6.73	0.250	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	8.89	9.65	0.350	0.380
L1	1.90	2.29	0.075	0.090
L2	0.89	1.37	0.035	0.054

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